

ABSTRACT OF THE DISCLOSURE

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There is provided, according to one embodiment of  
this invention, a semiconductor memory device  
~~including~~ comprising first memory elements to store a first state  
5 or a second state according to a change in resistance  
value, each of the first memory elements ~~including~~ comprising one  
terminal and the other terminal, the first memory  
elements arranged parallel with each other, a first  
wiring connected with the one terminal of each of the  
10 first memory elements, and a second wiring formed in  
parallel with the first wiring and connected with the  
other terminal of each of the first memory elements,  
wherein the first state or the second state stored in  
one of selected from the first memory elements is read  
15 out by delivering an electric current from one of the  
first and second wirings via the one of selected from  
the first memory elements to the other of the first and  
second wirings.